

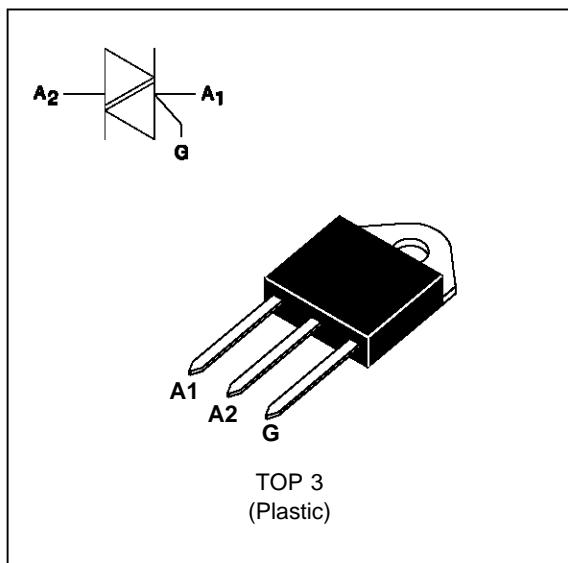
STANDARD TRIACS

FEATURES

- HIGH SURGE CURRENT CAPABILITY
- COMMUTATION : $(dV/dt)_c > 10V/\mu s$
- BTA Family :
INSULATING VOLTAGE = $2500V_{(RMS)}$
(UL RECOGNIZED : E81734)

DESCRIPTION

The BTA26 A/B / BTB26 B triac family are high performance glass passivated PNP devices. These parts are suitable for general purpose applications where high surge current capability is required. Application such as phase control and static switching on inductive or resistive load.



ABSOLUTE RATINGS (limiting values)

| Symbol | Parameter | | Value | Unit | |
|------------------------------------|---|-----|-------------------------|--------------------------------|------------------|
| I _{T(RMS)} | RMS on-state current (360° conduction angle) | BTA | T _c = 90 °C | 25 | A |
| | | BTB | T _c = 90 °C | 30 | |
| I _{TSM} | Non repetitive surge peak on-state current (T _j initial = 25°C) | | tp = 8.3 ms | 260 | A |
| | | | tp = 10 ms | 250 | |
| i ² t | i ² t value | | tp = 10 ms | 312.5 | A ² s |
| di/dt | Critical rate of rise of on-state current Gate supply : I _G = 500mA di _G /dt = 1A/μs | | Repetitive F = 50 Hz | 10 | A/μs |
| | | | Non Repetitive | 50 | |
| T _{stg} T _j | Storage and operating junction temperature range | | | - 40 to + 150 - 40 to + 125 | °C °C |
| TI | Maximum lead temperature for soldering during 10 s at 4.5 mm from case | | | 260 | °C |

| Symbol | Parameter | BTA26-...A/B / BTB26-... B | | | | Unit |
|--------------------------------------|--|----------------------------|-----|-----|-----|------|
| | | 400 | 600 | 700 | 800 | |
| V _{DRM} V _{RRM} | Repetitive peak off-state voltage T _j = 125 °C | 400 | 600 | 700 | 800 | V |

THERMAL RESISTANCES

| Symbol | Parameter | | Value | Unit |
|--------------|---|-----|-------|------|
| Rth (j-a) | Junction to ambient | | 50 | °C/W |
| Rth (j-c) DC | Junction to case for DC | BTA | 1.5 | °C/W |
| | | BTB | 1.1 | |
| Rth (j-c) AC | Junction to case for 360° conduction angle (F= 50 Hz) | BTA | 1.1 | °C/W |
| | | BTB | 0.8 | |

GATE CHARACTERISTICS (maximum values)

PG (AV) = 1W PGM = 40W (tp = 20 μs) IGM = 8A (tp = 20 μs) VGM = 16V (tp = 20 μs).

ELECTRICAL CHARACTERISTICS

| Symbol | Test Conditions | | Quadrant | | Suffix | | Unit |
|--------------|--|----------|-------------|-----|--------|-----|------|
| | | | | | A | B | |
| IGT | VD=12V (DC) RL=33Ω | Tj=25°C | I-II-III | MAX | 100 | 50 | mA |
| | | | IV | MAX | 150 | 100 | |
| VGT | VD=12V (DC) RL=33Ω | Tj=25°C | I-II-III-IV | MAX | 1.5 | | V |
| VGD | VD=VDRM RL=3.3kΩ | Tj=125°C | I-II-III-IV | MIN | 0.2 | | V |
| tgt | VD=VDRM IG = 500mA dIG/dt = 3A/μs | Tj=25°C | I-II-III-IV | TYP | 2.5 | | μs |
| IL | IG=1.2 IGT | Tj=25°C | I-III-IV | TYP | 70 | 60 | mA |
| | | | II | | 200 | 180 | |
| IH * | IT= 500mA gate open | Tj=25°C | | MAX | 100 | 80 | mA |
| VTM * | ITM= 35A tp= 380μs | Tj=25°C | | MAX | 1.7 | | V |
| IDRM IRRM | VDRM Rated VRRM Rated | Tj=25°C | | MAX | 0.01 | | mA |
| | | Tj=125°C | | MAX | 6 | | |
| dV/dt * | Linear slope up to VD=67%VDRM gate open | Tj=125°C | | MIN | 250 | 250 | V/μs |
| (dV/dt)c * | (dI/dt)c = 11.1A/ms BTA (dI/dt)c = 13.3A/ms BTB | Tj=125°C | | MIN | 10 | | V/μs |

* For either polarity of electrode A2 voltage with reference to electrode A1.

ORDERING INFORMATION

| Package | $I_T(\text{RMS})$ | $V_{\text{DRM}} / V_{\text{RRM}}$ | Sensitivity Specification | |
|----------------------|-------------------|-----------------------------------|---------------------------|---|
| | A | V | A | B |
| BTA (Insulated) | 26 | 400 | X | X |
| | | 600 | X | X |
| | | 700 | X | X |
| | | 800 | X | X |
| BTB (Uninsulated) | 30 | 400 | | X |
| | | 600 | | X |
| | | 700 | | X |
| | | 800 | | X |

Fig.1 : Maximum RMS power dissipation versus RMS on-state current (F=50Hz).
(Curves are cut off by (di/dt)c limitation) (BTA)

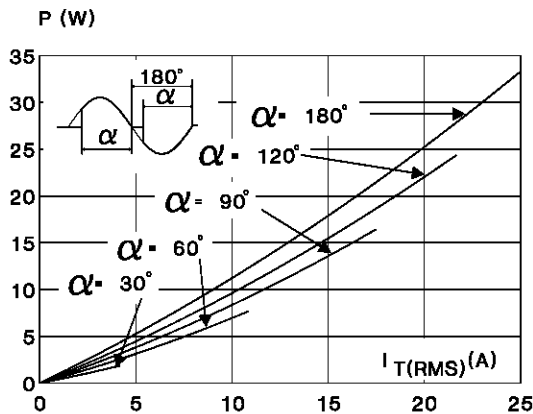


Fig.3 : Maximum RMS power dissipation versus RMS on-state current (F=50Hz).
(Curves are cut off by (di/dt)c limitation) (BTB)

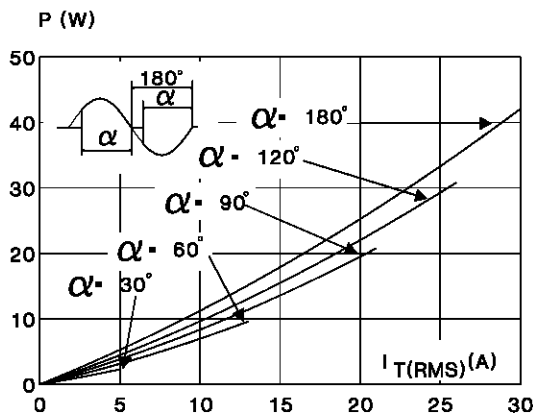


Fig.2 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTA).

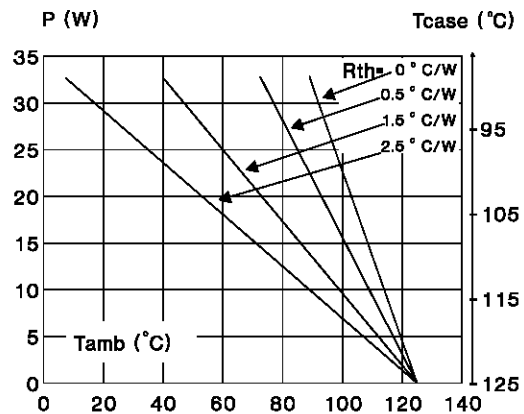
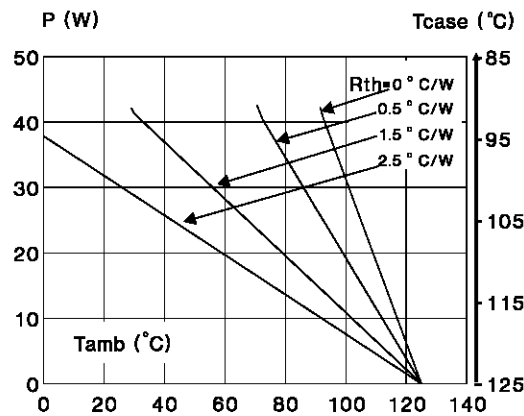


Fig.4 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTB).



BTA26 A/B / BTB26 B

Fig.5 : RMS on-state current versus case temperature. (BTA)

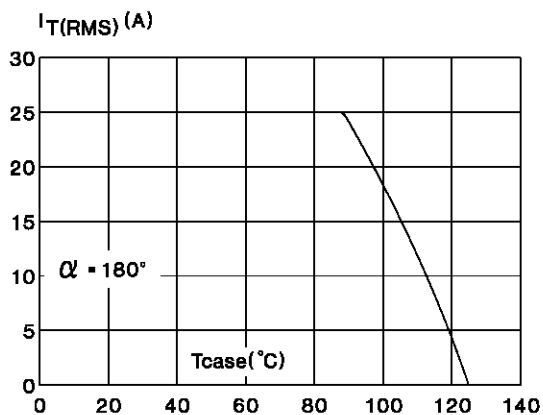


Fig.6 : RMS on-state current versus case temperature. (BTB)

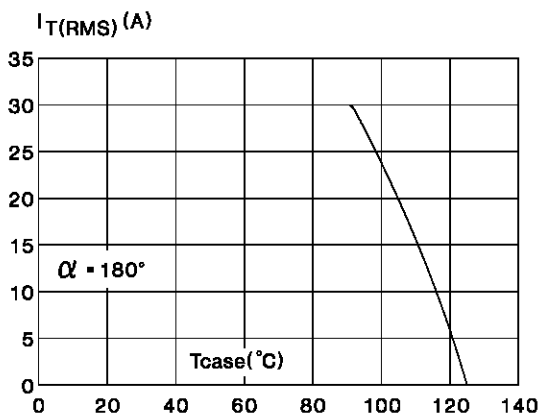


Fig.7 : Relative variation of thermal impedance versus pulse duration.

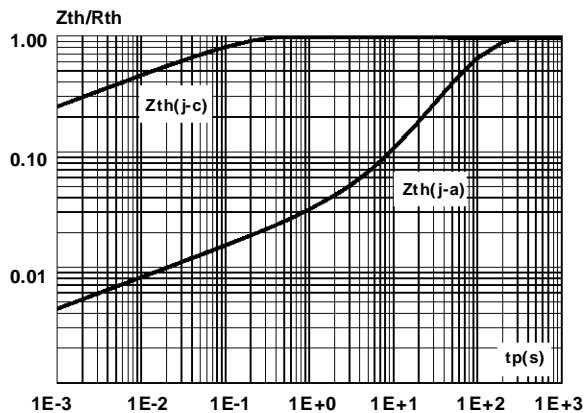


Fig.8 : Relative variation of gate trigger current and holding current versus junction temperature.

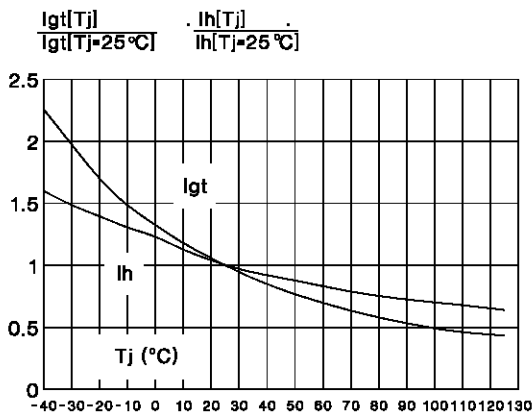


Fig.9 : Non Repetitive surge peak on-state current versus number of cycles.

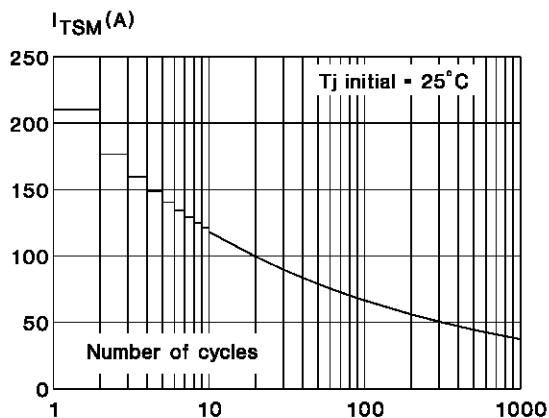


Fig.10 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leq 10\text{ms}$, and corresponding value of I^2t .

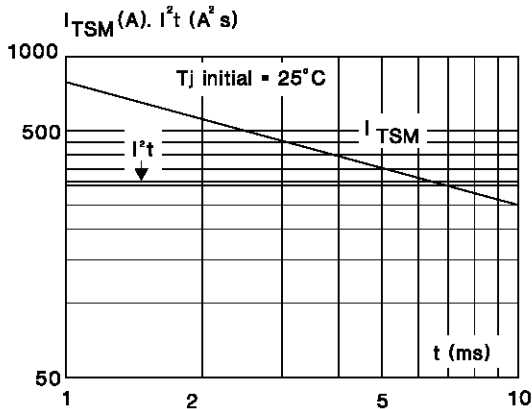
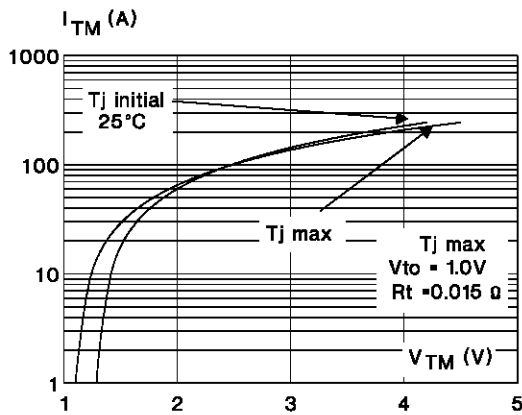
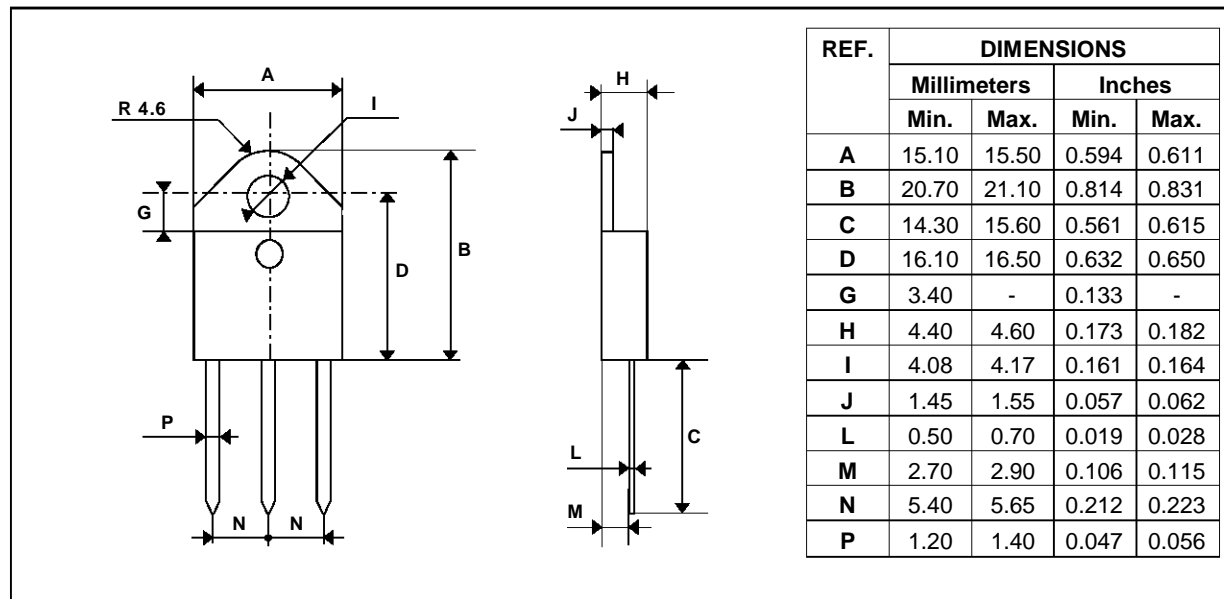


Fig.11 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA

TOP 3 Plastic



Cooling method : C
 Marking : type number
 Weight : 4.7 g

Recommended torque value : 0.8 m.N.
 Maximum torqure value : 1 m.N.

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